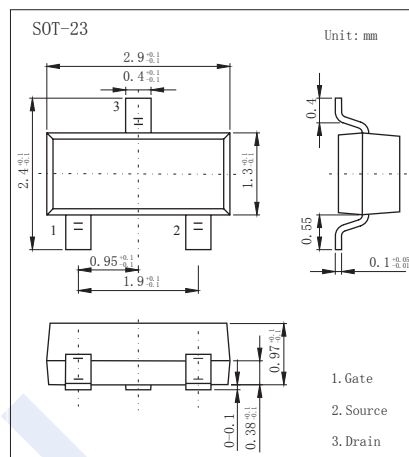


P-Channel Enhancement MOSFET

KI001P

■ Features

- $V_{DS} (V) = -12V$
- $I_D = -2.8 A$
- $R_{DS(on)} < 100m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(on)} < 150m\Omega$ ($V_{GS} = -2.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	-2.8	A
Power Dissipation	P_D	1.2	W
Junction Temperature	T_J	150	$^\circ C$
Junction and Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A$, $V_{GS} = 0V$	-12	-18		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V$, $V_{GS} = 0V$, $T_J = 25^\circ C$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-0.4	-0.7	-1.1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V$, $I_D = -1A$			100	$m\Omega$
		$V_{GS} = -2.5V$, $I_D = -0.5A$			150	